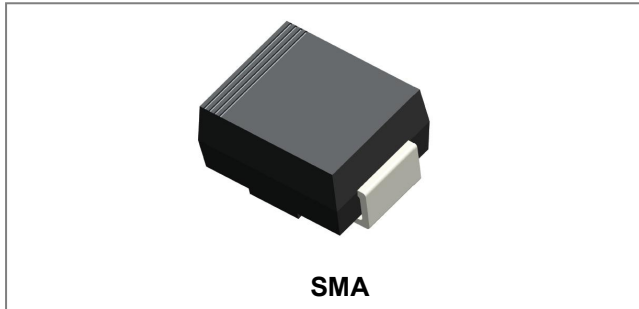


## 10MQ100N-S SCHOTTKY RECTIFIER



### Features

- Small foot print, surface moutable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Circuit Diagram



### Applications

- Disk Drives
- Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery Charging

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	$V_{RRM}$	-	100	V
Working Peak Reverse Voltage	$V_{RWM}$			
DC Blocking Voltage	$V_R$			
Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_L = 105^\circ\text{C}$ , rectangular wave form	1.5	A
DC Current	$I_{F(DC)}$	DC@ $T_L = 120^\circ\text{C}$	2.1	A
Peak One Cycle Non-Repetitive Surge Current	$I_{FSM}$	8.3 ms, half Sine pulse	36	A

### Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	$V_{F1}$	@ 1 A, Pulse, $T_J = 25^\circ\text{C}$	0.76	0.78	V
		@ 1.5 A, Pulse, $T_J = 25^\circ\text{C}$	0.79	0.85	
Reverse Current*	$V_{F2}$	@ 1 A, Pulse, $T_J = 125^\circ\text{C}$	0.60	0.63	V
		@ 1.5A, Pulse, $T_J = 125^\circ\text{C}$	0.64	0.68	
Reverse Current*	$I_{R1}$	@ $V_R = \text{rated } V_R$ , Pulse, $T_J = 25^\circ\text{C}$	0.01	100	$\mu\text{A}$
	$I_{R2}$	@ $V_R = \text{rated } V_R$ , Pulse, $T_J = 125^\circ\text{C}$	0.009	1	mA
Junction Capacitance	$C_T$	@ $V_R = 5\text{V}$ , $T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	27	38	PF
Typical Series Inductance	$L_S$	Measured lead to lead 5 mm from package body	2.0	-	nH
Voltage Rate of Change	$dv/dt$	-	-	10,000	$\text{V}/\mu\text{s}$

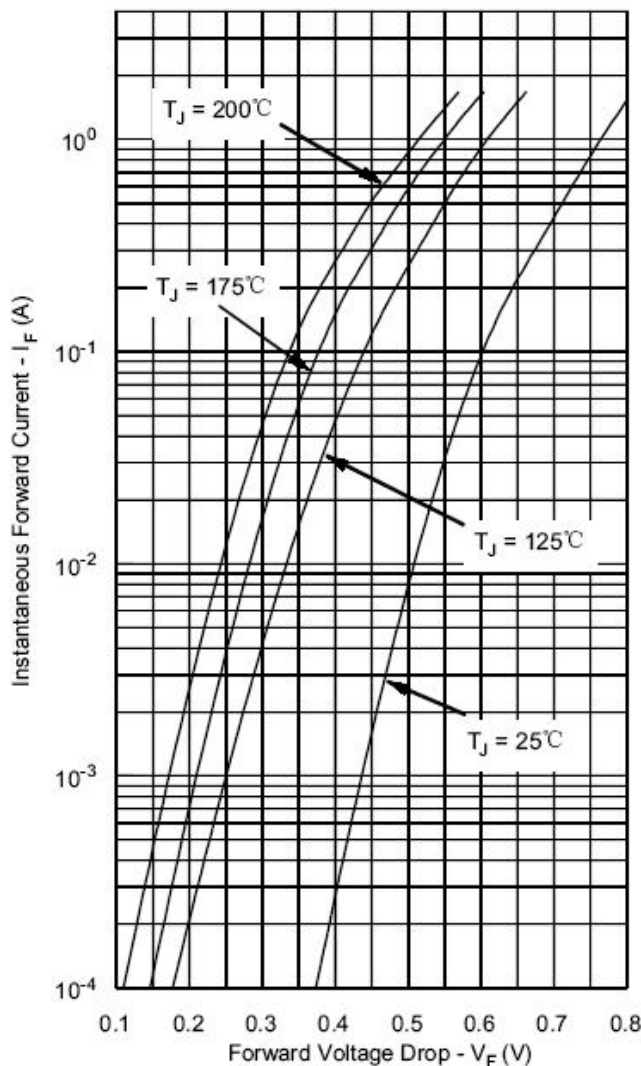
\* Pulse width < 300  $\mu\text{s}$ , duty cycle < 2%

**Thermal-Mechanical Specifications:**

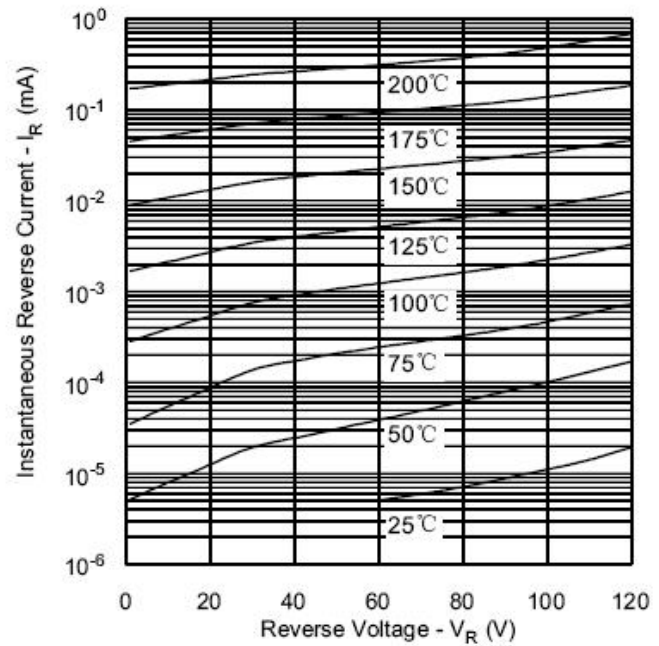
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_J$	-	-55 to +150	$^{\circ}\text{C}$
Storage Temperature	$T_{\text{stg}}$	-	-55 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Ambient	$R_{\theta JA}$	-	80	$^{\circ}\text{C/W}$
Approximate Weight	wt	-	0.06	g
Case Style		SMA		

**Ratings and Characteristics Curves**

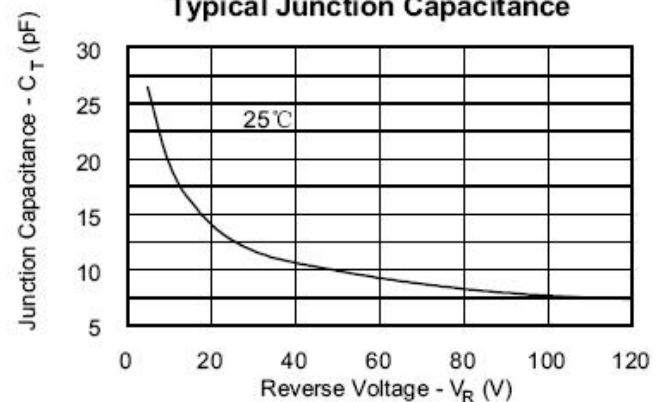
Typical Forward Characteristics



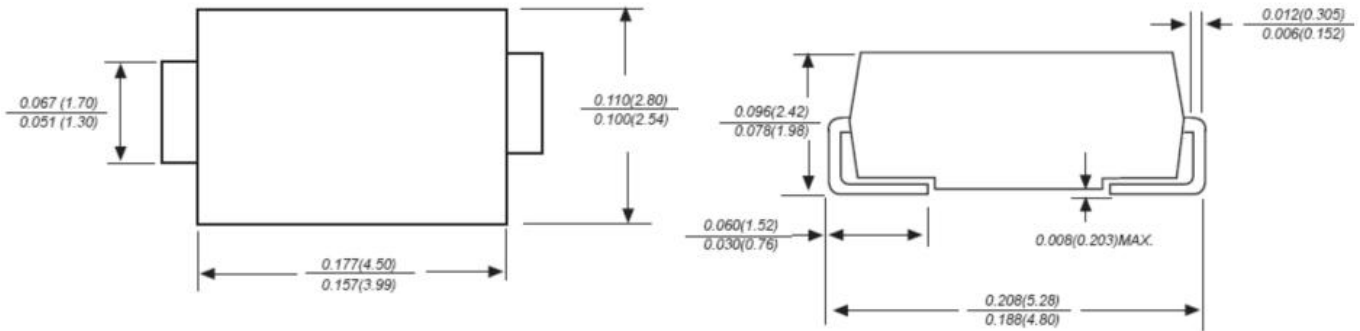
Typical Reverse Characteristics



Typical Junction Capacitance



**Mechanical Dimensions SMA(Millimeters/Inches)**

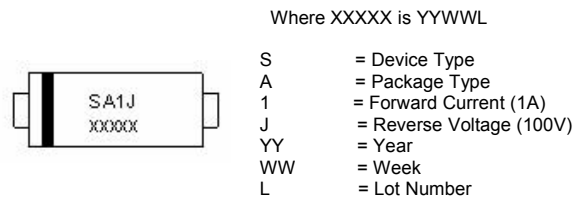


**Ordering Information**

Device	Package	Shipping
10MQ100N-S	SMA (Pb-Free)	5000pcs / reel

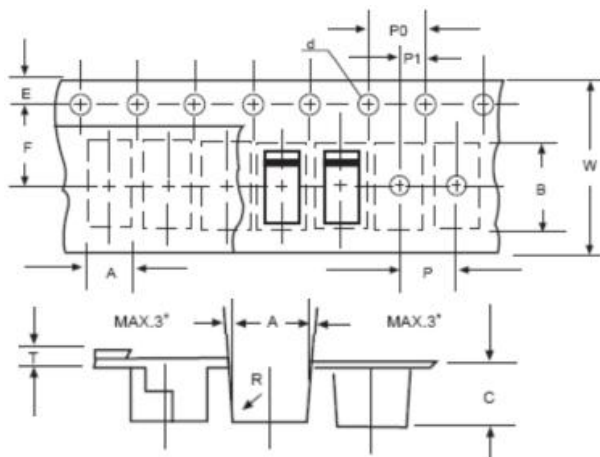
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

**Marking Diagram**



**Cautions:** Molding resin  
Epoxy resin UL:94V-0

**Carrier Tape & Reel Specification SMA**



SYMBOL	Millimeters	
	Min.	Max.
A	2.97	3.17
B	5.70	5.90
C	2.32	2.52
d	1.40	1.60
E	1.40	1.60
F	5.60	5.70
P	3.90	4.10
P0	3.90	4.10
P1	1.90	2.10
T	0.25	0.35
W	11.80	12.20

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